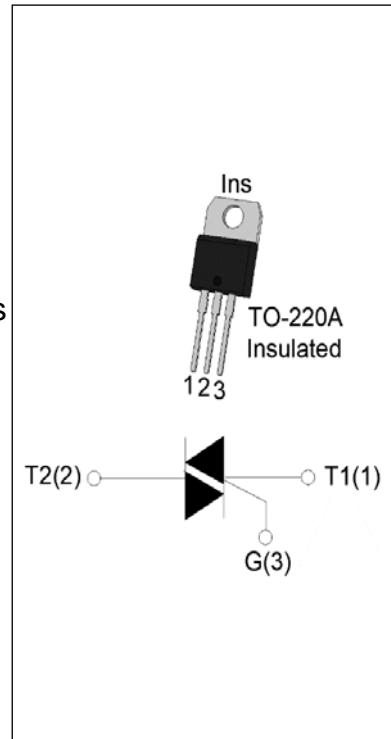


**DESCRIPTION:**

The JST06A-800BW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST06A-800BW snubberless triac is especially recommended for use on inductive loads. By using an internal ceramic pad, JST06A-800BW provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_T(\text{RMS})$	6	A
$V_{\text{DRM}} / V_{\text{RRM}}$	800	V
$I_{\text{GT I/II/III}}$	50/50/50	mA

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{\text{stg}}$	-40-150	°C
Operating junction temperature range	$T_j$	-40-125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{\text{DRM}}$	800	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{\text{RRM}}$	800	V
RMS on-state current ( $T_c \leq 100^\circ\text{C}$ )	$I_T(\text{RMS})$	6	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I_{\text{TSM}}$	65	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )		72	
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I^2t$	21	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{\text{GT}}$ , $f=100\text{Hz}$ , $T_j=125^\circ\text{C}$ )	$dI/dt$	100	$\text{A}/\mu\text{s}$
Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$ )	$I_{\text{GM}}$	4	A
Average gate power dissipation ( $T_j=125^\circ\text{C}$ )	$P_{\text{G(AV)}}$	0.5	W
Peak gate power	$P_{\text{GM}}$	10	W

Peak pulse voltage (T <sub>j</sub> =25°C; non-repetitive,off-state;FIG.7)	V <sub>PP</sub>	4	kV
------------------------------------------------------------------------------	-----------------	---	----

**ELECTRICAL CHARACTERISTICS (T<sub>j</sub>=25°C unless otherwise specified)**

Symbol	Test Condition	Quadrant	Value		Unit
I <sub>GT</sub>	V <sub>D</sub> =12V R <sub>L</sub> =33Ω	I - II -III	MAX.	50	mA
V <sub>GT</sub>		I - II -III	MAX.	1	V
V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> T <sub>j</sub> =125°C R <sub>L</sub> =3.3KΩ	I - II -III	MIN.	0.2	V
I <sub>L</sub>	I <sub>G</sub> =1.2I <sub>GT</sub>	I - III	MAX.	70	mA
		II		80	
I <sub>H</sub>	I <sub>T</sub> =100mA		MAX.	50	mA
dV/dt	V <sub>D</sub> =540V Gate Open T <sub>j</sub> =125°C		MIN.	1500	V/μs
(dI/dt)c	(dV/dt)c=20V/μs, T <sub>j</sub> =125°C		MIN.	8	A/ms
t <sub>on</sub>	I <sub>G</sub> =80mA I <sub>A</sub> =400mA I <sub>R</sub> =40mA T <sub>j</sub> =25°C	TYP.	5	μs	
t <sub>off</sub>			50		

**STATIC CHARACTERISTICS**

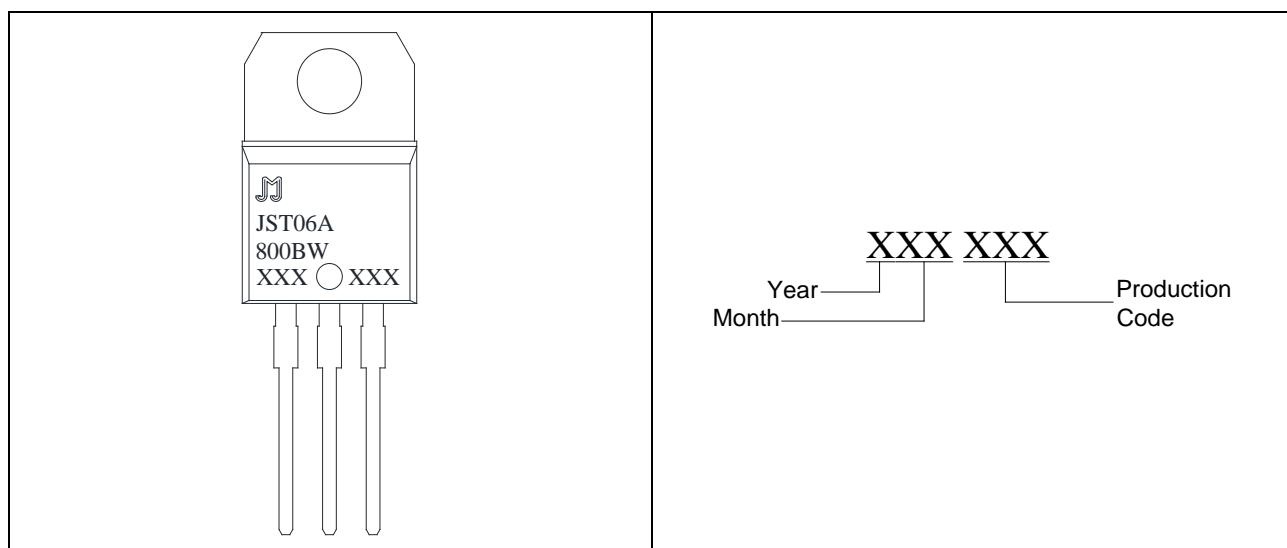
Symbol	Parameter		Value(MAX.)	Unit
V <sub>TM</sub>	I <sub>TM</sub> =8.5A t <sub>p</sub> =380μs	T <sub>j</sub> =25°C	1.5	V
V <sub>TO</sub>	Threshold voltage	T <sub>j</sub> =125°C	0.82	V
R <sub>D</sub>	Dynamic resistance	T <sub>j</sub> =125°C	57	mΩ
I <sub>DRM</sub>	V <sub>D</sub> =V <sub>DRM</sub> V <sub>R</sub> =V <sub>RRM</sub>	T <sub>j</sub> =25°C	5	μA
I <sub>RRM</sub>		T <sub>j</sub> =125°C	0.3	mA

**THERMAL RESISTANCES**

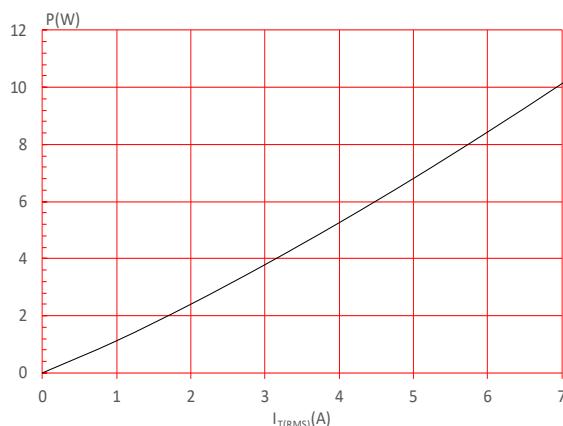
Symbol	Parameter	Value	Unit
R <sub>th(j-c)</sub>	junction to case (AC)	3	°C/W
R <sub>th(j-a)</sub>	junction to ambient (AC)	60	°C/W

**ORDERING INFORMATION**

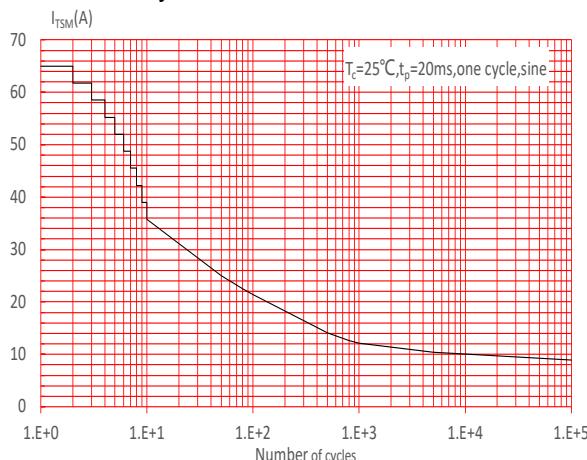
<u>J</u>	<u>ST</u>	<u>06</u>	<u>A</u>	<u>-800</u>	<u>BW</u>
JieJie Microelectronics Co., Ltd.					
	Triacs				
		IT(RMS):6A			
			A:TO-220A(Ins)		
				BW:IGT1-3≤50mA	
				800:VDRM /VRRM ≥800V	

**MARKING**

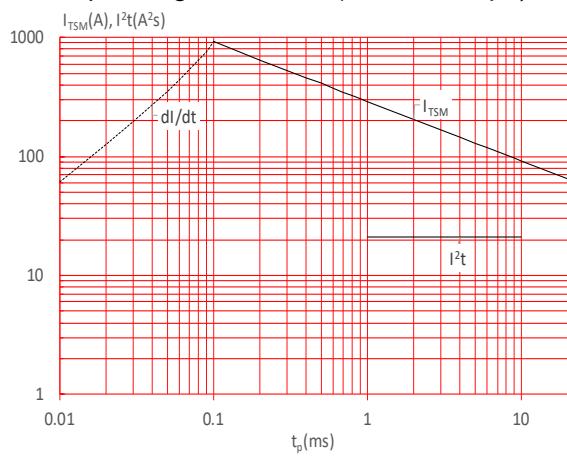
**FIG.1** Maximum power dissipation versus RMS on-state current



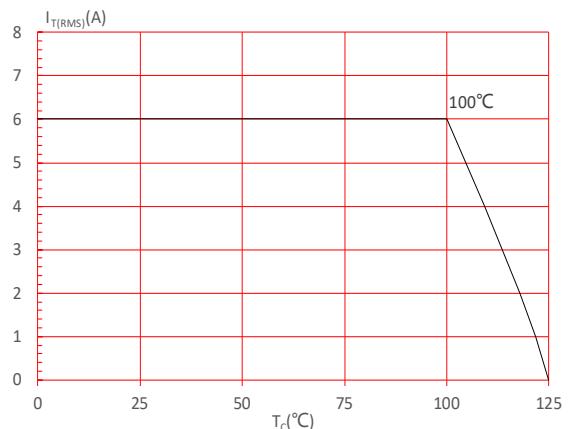
**FIG.3:** Surge peak on-state current versus number of cycles



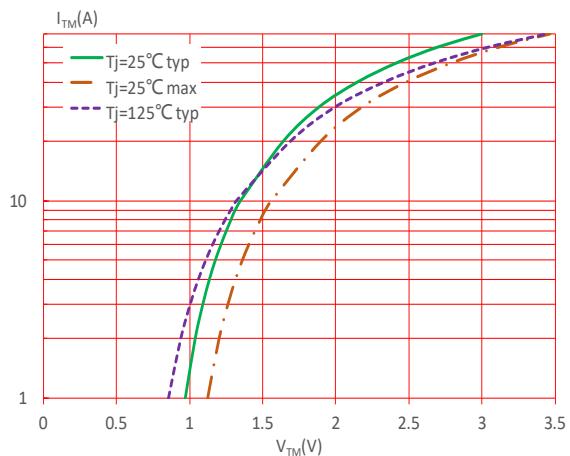
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $dI/dt < 100\text{A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

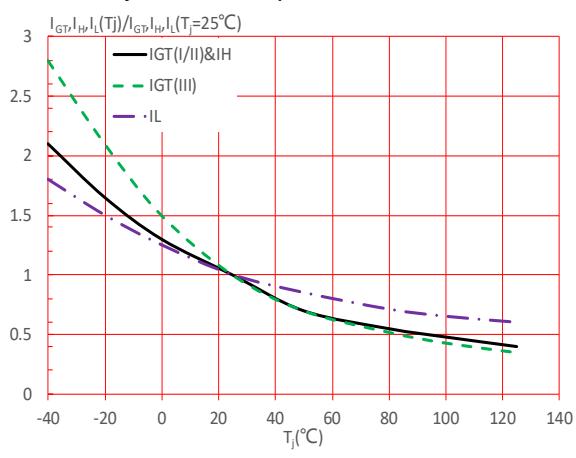
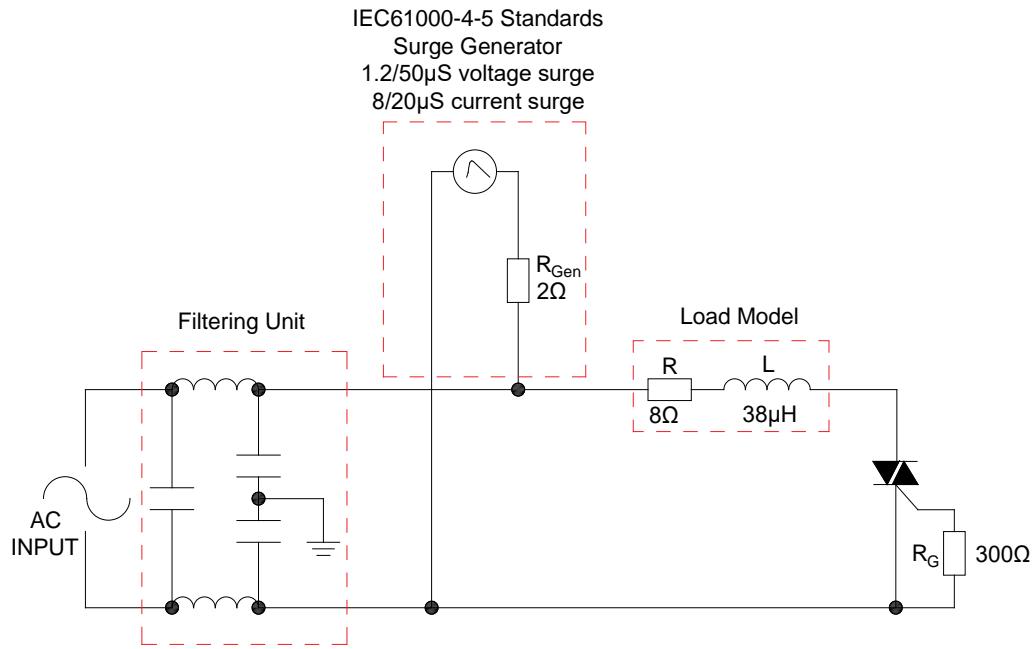


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



## SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie

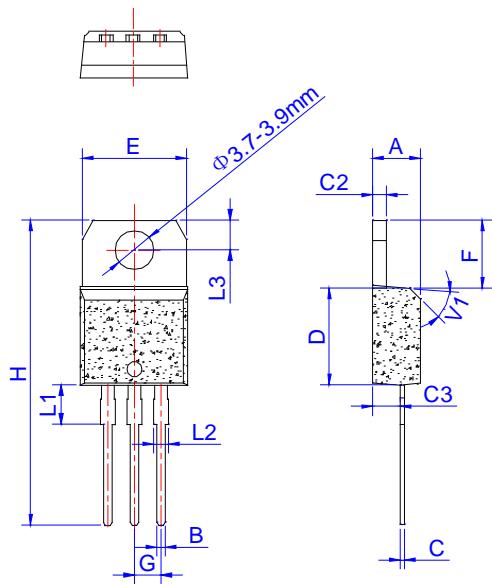
**ORDERING INFORMATION**

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I - II - III			
<b>JST06A-800BW</b>	<b>800</b>	<b>50</b>	<b>TO-220A(Ins)</b>	<b>50</b>	<b>Tube</b>

**Document Revision History**

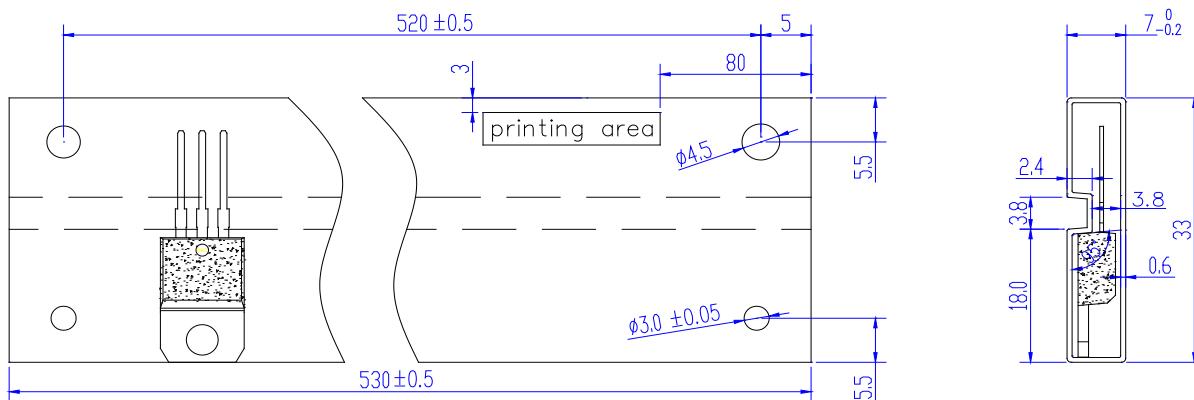
Date	Revision	Changes
Apr.11, 2023	A.1.0	Last updated

## PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.25		6.85	0.246		0.270
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	3.45		4.05	0.136		0.159
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

## DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220A	TUBE	50	1,000	5,000

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